

PSMN012-100YS

N-channel 100V 12m Ω standard level MOSFET in LFPAK

Rev. 04 — 23 February 2010

Product data sheet

1. Product profile

1.1 General description

Standard level N-channel MOSFET in LFPAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- Advanced TrenchMOS provides low RDSon and low gate charge
- High efficiency gains in switching power converters
- Improved mechanical and thermal characteristics
- LFPAK provides maximum power density in a Power SO8 package

1.3 Applications

- DC-to-DC converters
- Lithium-ion battery protection
- Load switching

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1. Quick reference

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	100	V
I _D	drain current	T _{mb} = 25 °C; see <u>Figure 1</u>	-	-	60	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	130	W
Tj	junction temperature		-55	-	175	°C
Avalanche ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 60 A; $V_{sup} \le$ 100 V; R_{GS} = 50 Ω; unclamped	-	-	170	mJ
Dynamic	characteristics					
Q_{GD}	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 45 \text{ A};$	-	19	-	nC
$Q_{G(tot)}$	total gate charge	V _{DS} = 50 V; see <u>Figure 14</u> and <u>15</u>	-	64	-	nC



Table 1. Quick reference ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics					
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A};$ $T_j = 100 \text{ °C}; \text{ see } \frac{\text{Figure } 12}{}$	-	-	23	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A};$ $T_j = 25 ^{\circ}\text{C}; \text{ see } \frac{\text{Figure } 13}{\text{Figure } 13}$	-	10	12	mΩ

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		_
2	S	source	mb	D
3	S	source		
4	G	gate	[Q]	
mb	D	mounting base; connected to drain	1 2 3 4	mbb076 Ś
			SOT669 (LFPAK)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN012-100YS	LFPAK	plastic single-ended surface-mounted package (LFPAK); 4 leads	SOT669

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	100	V
V_{DGR}	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	100	V
V_{GS}	gate-source voltage		-20	20	V
I _D	drain current	T _{mb} = 100 °C; see <u>Figure 1</u>	-	43	Α
		T _{mb} = 25 °C; see <u>Figure 1</u>	-	60	Α
I_{DM}	peak drain current	$t_p \le 10 \mu s$; pulsed; $T_{mb} = 25 \text{ °C}$; see Figure 3	-	242	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	130	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T _{sld(M)}	peak soldering temperature		-	260	°C
Source-dr	ain diode				
Is	source current	T _{mb} = 25 °C	-	60	Α
I _{SM}	peak source current	$t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ}C$	-	242	Α
Avalanche	ruggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 60 A; V_{sup} ≤ 100 V; R_{GS} = 50 Ω; unclamped	-	170	mJ

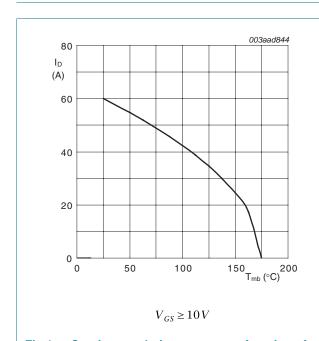


Fig 1. Continuous drain current as a function of mounting base temperature

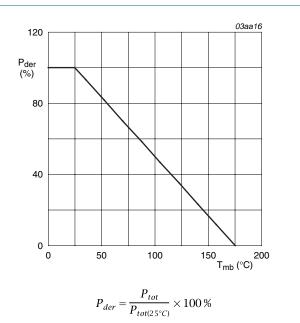
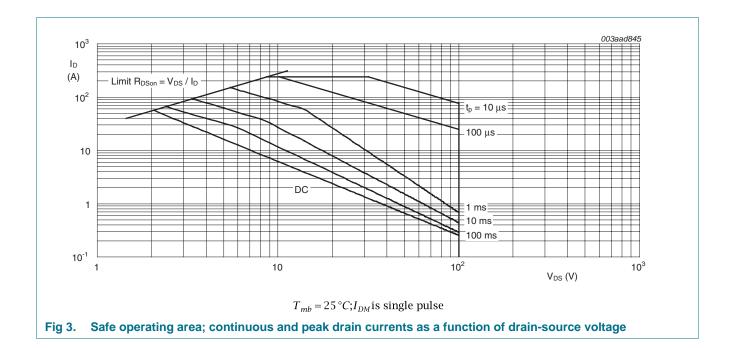


Fig 2. Normalized total power dissipation as a function of mounting base temperature



5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.5	1.1	K/W

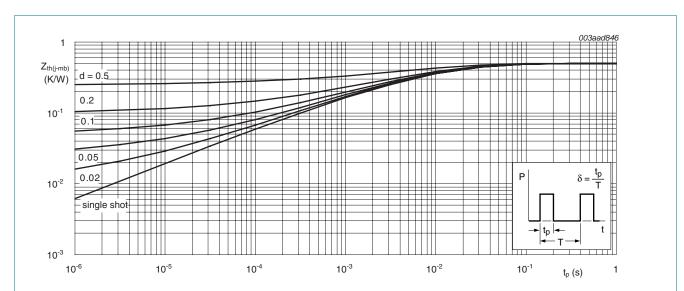


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values

6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V _{(BR)DSS} drain-source		$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	90	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	100	-	-	V
$V_{\text{GS(th)}}$	gate-source threshold voltage	$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 175 \text{ °C}$; see Figure 10	0.95	-	-	V
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; see <u>Figure 11</u> and <u>10</u>	2	3	4	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = -55$ °C; see Figure 10	-	-	4.6	V
I _{DSS}	drain leakage current	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$	-	-	100	μΑ
		$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.06	5	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 100 \text{ °C};$ see Figure 12	-	-	23	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 175 \text{ °C};$ see Figure 12	-	27	35.8	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 13	-	10	12	mΩ
R_{G}	internal gate resistance (AC)	f = 1 MHz	-	0.7	-	Ω
Dynamic (characteristics					
Q _{G(tot)}	total gate charge	$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	51	-	nC
		$I_D = 45 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$	-	64	-	nC
Q_{GS}	gate-source charge	see <u>Figure 14</u> and <u>15</u>	-	14.9	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	$I_D = 45 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14	-	10.2	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	4.7	-	nC
Q_{GD}	gate-drain charge	$I_D = 45 \text{ A}$; $V_{DS} = 50 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 14 and 15	-	19	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$V_{DS} = 50 \text{ V}$; see <u>Figure 14</u> and <u>15</u>	-	4.4	-	V
C _{iss}	input capacitance	$V_{DS} = 50 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}; T_j = 25 °C;$	-	3500	-	pF
C _{oss}	output capacitance	see Figure 16	-	246	-	pF
C _{rss}	reverse transfer capacitance		-	149	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 50 \text{ V}; R_L = 1.1 \Omega; V_{GS} = 10 \text{ V};$	-	23	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \ \Omega; T_j = 25 \ ^{\circ}C$	-	31	-	ns
t _{d(off)}	turn-off delay time		-	52.5	-	ns
t _f	fall time		-	25	-	ns

Table 6. Characteristics ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-dr	ain diode					
V_{SD}	source-drain voltage	$I_S = 15 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 \text{ °C}$; see <u>Figure 17</u>	-	8.0	1.2	V
t _{rr}	reverse recovery time	$I_S = 15 \text{ A}$; $dI_S/dt = 100 \text{ A/}\mu\text{s}$; $V_{GS} = 0 \text{ V}$;	-	56	-	ns
Q _r	recovered charge	$V_{DS} = 50 \text{ V}$	-	129	-	nC

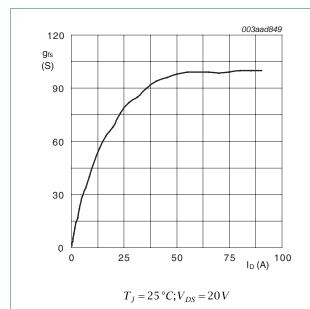


Fig 5. Forward transconductance as a function of drain current; typical values

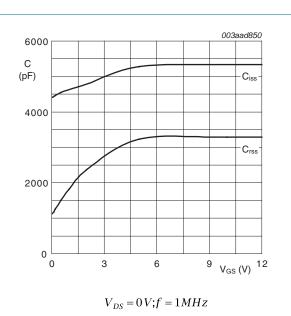


Fig 6. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

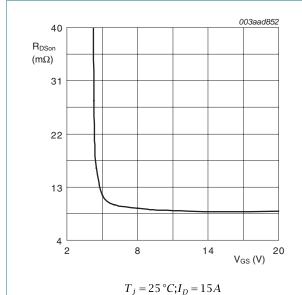


Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

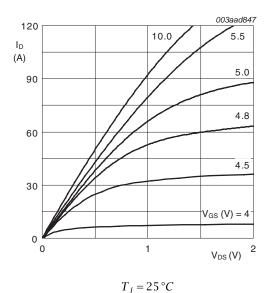


Fig 8. Output characteristics: drain current as a function of drain-source voltage; typical values

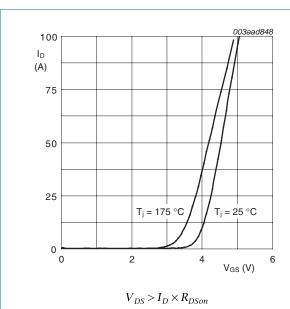
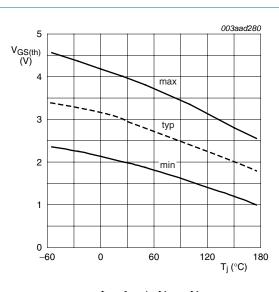
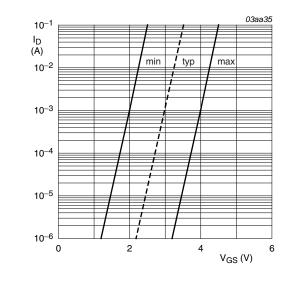


Fig 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values



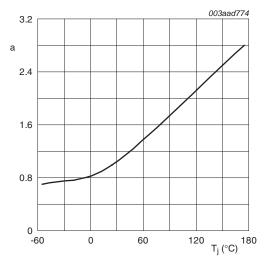
 $I_D = 1$ mA; $V_{DS} = V_{GS}$

Fig 10. Gate-source threshold voltage as a function of junction temperature



 $T_j = 25 \,^{\circ}C; V_{DS} = 5V$

Fig 11. Sub-threshold drain current as a function of gate-source voltage



$$=\frac{R_{DSon}}{R_{DSon(25\,^{\circ}\text{C})}}$$

Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature

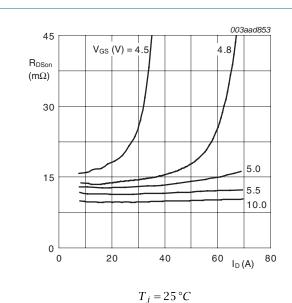


Fig 13. Drain-source on-state resistance as a function of drain current; typical values

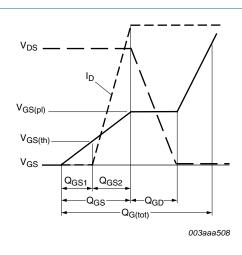


Fig 14. Gate charge waveform definitions

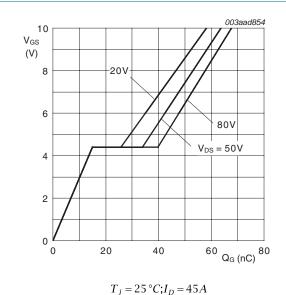
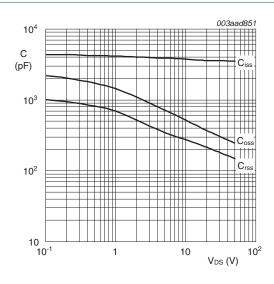
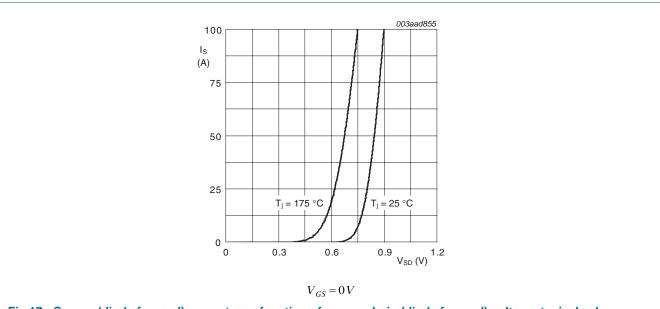


Fig 15. Gate-source voltage as a function of gate charge; typical values



 $V_{GS} = 0V; f = 1MHz$

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



7. Package outline

Plastic single-ended surface-mounted package (LFPAK); 4 leads

SOT669

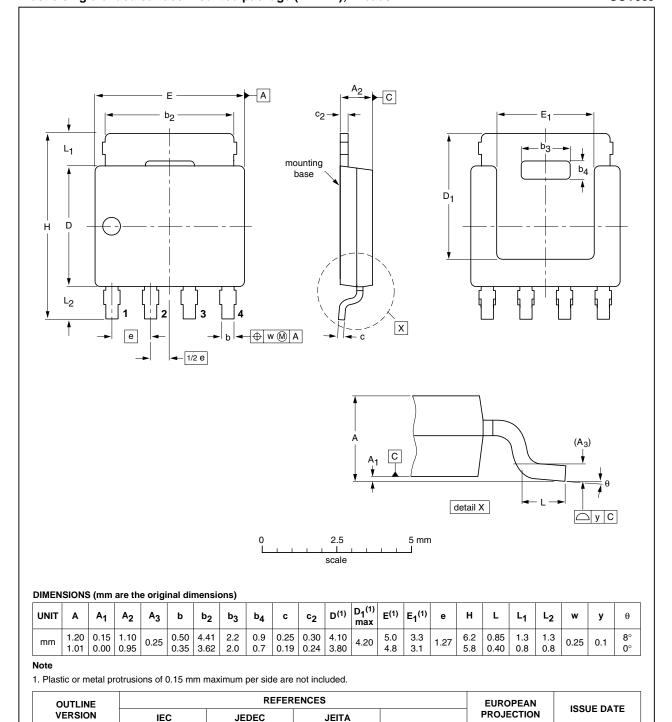


Fig 18. Package outline SOT669 (LFPAK)

PSMN012-100YS_4

All information provided in this document is subject to legal disclaimers.

MO-235

04-10-13

06-03-16

SOT669

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN012-100YS_4	20100223	Product data sheet	-	PSMN012-100YS_3
Modifications:	 Status char 	nged from objective to pro	duct.	
PSMN012-100YS_3	20100107	Product data sheet	-	PSMN012-100YS_2
PSMN012-100YS_2	20091214	Objective data sheet	-	PSMN012-100YS_1
PSMN012-100YS_1	20091022	Objective data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status [1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nexperia.com.

9.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. Nexperia does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local Nexperia sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

Product specification — The information and data provided in a Product data sheet shall define the specification of the product as agreed between Nexperia and its customer, unless Nexperia and customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the Nexperia product is deemed to offer functions and qualities beyond those described in the Product data sheet.

9.3 Disclaimers

Limited warranty and liability — Information in this document is believed to be accurate and reliable. However, Nexperia does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

In no event shall Nexperia be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, Nexperia's aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the *Terms and conditions of commercial sale* of Nexperia.

Right to make changes — Nexperia reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — Nexperia products are not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or malfunction of a Nexperia product can reasonably be expected to result in personal injury, death or severe property or environmental damage. Nexperia accepts no liability for inclusion and/or use of Nexperia products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. Nexperia makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Nexperia does not accept any liability related to any default, damage, costs or problem which is based on a weakness or default in the customer application/use or the application/use of customer's third party customer(s) (hereinafter both referred to as "Application"). It is customer's sole responsibility to check whether the Nexperia product is suitable and fit for the Application planned. Customer has to do all necessary testing for the Application in order to avoid a default of the Application and the product. Nexperia does not accept any liability in this respect.

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

Terms and conditions of commercial sale — Nexperia products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nexperia.com/profile/terms, unless otherwise agreed in a valid written individual agreement. In case an individual agreement is concluded only the terms and conditions of the respective agreement shall apply. Nexperia hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of Nexperia products by customer.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

PSMN012-100YS_4

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from national authorities.

Non-automotive qualified products — Unless the data sheet of an Nexperia product expressly states that the product is automotive qualified, the product is not suitable for automotive use. It is neither qualified nor tested in accordance with automotive testing or application requirements. Nexperia accepts no liability for inclusion and/or use of non-automotive qualified products in automotive equipment or applications. In the event that customer uses the product for design-in and use in automotive applications to automotive specifications and standards, customer (a) shall use the product without Nexperia's warranty of the product for such automotive applications, use and specifications, and (b) whenever

customer uses the product for automotive applications beyond Nexperia' specifications such use shall be solely at customer's own risk, and (c) customer fully indemnifies Nexperia for any liability, damages or failed product claims resulting from customer design and use of the product for automotive applications beyond Nexperia's standard warranty and Nexperia's product specifications.

9.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

10. Contact information

For more information, please visit: http://www.nexperia.com

For sales office addresses, please send an email to: salesaddresses@nexperia.com

PSMN012-100YS

Nexperia

N-channel 100V 12m Ω standard level MOSFET in LFPAK

11. Contents

1	Product profile
1.1	General description
1.2	Features and benefits1
1.3	Applications
1.4	Quick reference data1
2	Pinning information
3	Ordering information
4	Limiting values3
5	Thermal characteristics5
6	Characteristics6
7	Package outline
8	Revision history12
9	Legal information13
9.1	Data sheet status
9.2	Definitions13
9.3	Disclaimers
9.4	Trademarks14
10	Contact information 14



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов:
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001:
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)

Факс: 8 (812) 320-02-42

Электронная почта: <u>org@eplast1.ru</u>

Адрес: 198099, г. Санкт-Петербург, ул. Калинина,

дом 2, корпус 4, литера А.